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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/772,283	02/06/2004	Saichirou Kaneko	50195-414	4944
75	90 10/18/2004		EXAM	INER
McDERMOTT, WILL & EMERY			ABRAHAM, FETSUM	
600 13th Street, N.W. Washington, DC 20005-3096			ART UNIT	PAPER NUMBER
		•	2826 DATE MAILED: 10/18/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
	10/772,283	KANEKO ET AL.
Office Action Summary	Examiner	Art Unit
	Fetsum Abraham	2826
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	correspondence address
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.1: after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period v - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be tin y within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from , cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).
Status		
1) Responsive to communication(s) filed on		
2a) ☐ This action is <b>FINAL</b> . 2b) ☑ This	action is non-final.	•
3) Since this application is in condition for allowar closed in accordance with the practice under E	•	
Disposition of Claims		
4) ☐ Claim(s) 1-28 is/are pending in the application. 4a) Of the above claim(s) is/are withdray 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-28 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	wn from consideration.	
Application Papers		•
9)☐ The specification is objected to by the Examine	r.	
10)☐ The drawing(s) filed on is/are: a)☐ acce	-	
Applicant may not request that any objection to the		
Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Ex		• • •
Priority under 35 U.S.C. § 119	•	
12) △ Acknowledgment is made of a claim for foreign a) △ All b) ☐ Some * c) ☐ None of:  1. △ Certified copies of the priority documents 2. ☐ Certified copies of the priority documents 3. ☐ Copies of the certified copies of the priority appligation from the International Bureau	s have been received. s have been received in Applicati rity documents have been receive	on No
* See the attached detailed Office action for a list	of the certified copies not receive	ed.
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	4)	
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)	5) 🔲 Notice of Informal P	atent Application (PTO-152)
Paper No(s)/Mail Date	6)	

Application/Control Number: 10/772,283

Art Unit: 2826

## **DETAILED ACTION**

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claim 28 recites the limitation "the second impurity" in claim 24. There is insufficient antecedent basis for this limitation in the claim.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-27 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yamamoto et al (6,737,722).

As for claims 1-3, the patent discloses a SiC based BJT (see column 11, 10-20) in the front page having a graded base region defined by the profile shown in figure 4 where the carrier density of the base at the emitter/base junction exceeds that of at the base/collector junction and the rest of the base region. Clearly, depletion is inherent at the junctions whether in application of reverse biased or in the absence of bias application. Although the claim language may not be duplicated in the art, it is clear that at small bias voltage or no bias voltage in the structure, the concentration of carriers at the base/emitter junction still exceeds that of in the bulk base region for a person skilled in the art to find this conclusion obvious since there is close to two order of magnitude more carriers at the junction than at the collector/base junction of the transistor.

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As for claims 9-20, the end result of the method claims converges to the structural claim in the preamble. Besides, "product by process" claims are directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See also In re Brown, 173 USPQ 685 and In re Thorpe, 227 USPQ 964, 966. Therefore, the way the product was made does not carry any patentable weight as long as the claims are directed to a device. Further, note that the applicant has the burden of proof in such cases, as the above case law makes clear. Also see MPEP 2113.

As for claims 21,22, the emitter is patterned to be formed inside the base and the punchthrough protection layer implies the increases doping profile of the base at the emitter/base junction and the dopant material of the base is clearly the opposite type of that of the emitter and the collector.

As for claims 23,24, the base layer is epitaxially grown and the base can also be a SiC material as indicated above.

As for claims 25,26, the specifically claimed band gap is a function of impurity density, which is a known variable in the art that depends on a specific application.

As for claim 27, boron is a known material for producing P-type semiconductor layer.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fetsum Abraham whose telephone number is: 571-272-1911. The examiner can normally be reached on 8:00 - 18:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J Flynn can be reached on 571-272-1915.

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